





Submicron Magnetometers and their Applications to the Study of Nanomagnetism and Biosensing

Stephan von Molnár

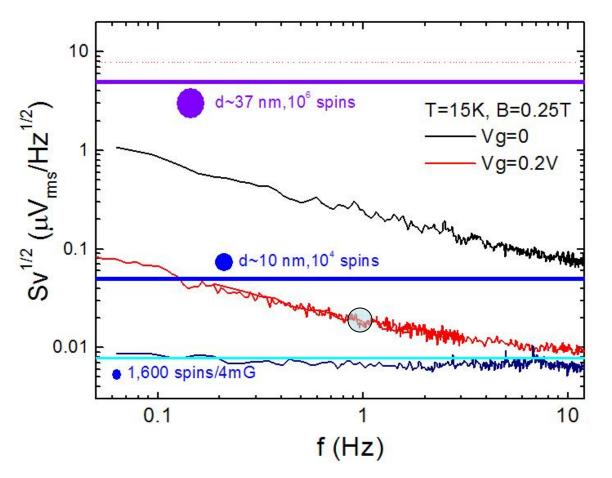
Department of Physics and Center for Materials Research and Technology Florida State University

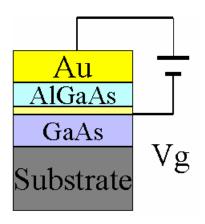
work supported by NSF grant DMR0072395, and by DARPA through ONR grants N-000014-99-1-1094 and MDA-972-02-1-0002

Acknowledgements

- P. Bryant Chase, Biological Sciences and Molecular Biophysics
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- Goran Mihajlović, MARTECH
- Jens Müller, MARTECH
- Hideo Ohno & Keita Ohtani, Tohoku University
- Mark Field & Gerard J. Sullivan, Rockwell Scientific Company LLC

Sensitivity of a Submicron Hall Device





Moment sensitivity:

$$\sim 10^4 \,\mu_{\rm B}/\sqrt{\rm Hz}$$

 $\sim 10^{-16} \,\rm emu$
@ B=0.25 T

Estimated for a dipole placed in the center of a Hall cross of physical size of $0.7X0.7\mu m^2$ and active area of $\sim 0.5X0.5 \ \mu m^2$

Kent, von Molnár, Gider, and Awschalom, J. Appl. Phys. (1994). Li et al., PRL (2004)

Outline

- Interaction effects at small scales
- I. Noise in submicron Hall devices
- **II.** Magnetic Biosensors

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- Interaction effects at small scales
- II. Noise in submicron Hall devices
- **III.** Magnetic Biosensors

Jens Müller

Materials by:

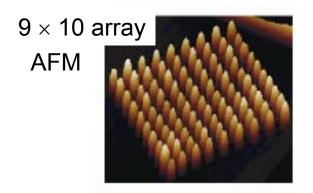
Hideo Ohno, Keita Ohtani (Tohoku University),

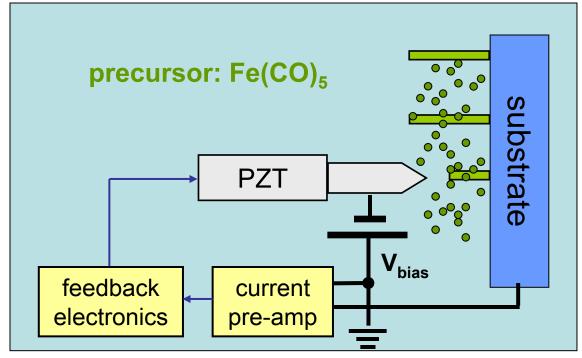
Nano-scale magnetic particles

- testing of theoretical models
- technological applications
- → high-density information storage
- → spin electronic devices

- growth by STM assisted CVD
 - → exact positioning
 - → d ~ 5 20 nm
 h ~ 80 250 nm
 a > 80 nm

a ≥ 80 nm

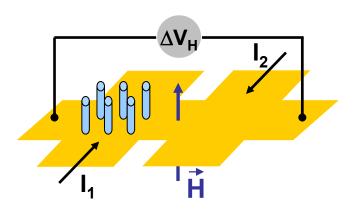




shape anisotropy: EMD along cylinder axis

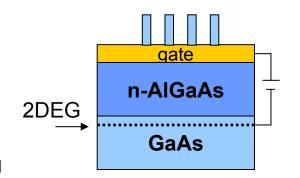
McCord and Awschalom, APL, (1990) Kent, Shaw, von Molnár, and Awschalom, Science, (1993)

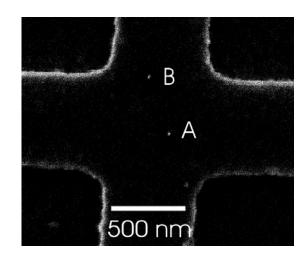
Micro-Hall magnetometry



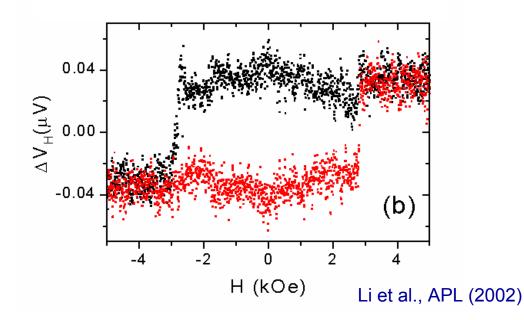
- Hall magnetometers based on 2DES in gated GaAs/Al_xGa_{1-x}As
 - → moment sensitivity ~ $10^4 \mu_B/\sqrt{\text{Hz}}$ @ 1 Hz Li et al., PRL (2004)

• measuring <B_z> → magnetization reversal of *individual* non-interacting particles grown on Au





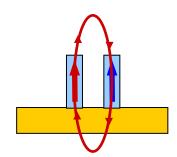
d ~ 5 nm, h ~ 120 nm, m ~ 5 \times $10^5 \mu_B$

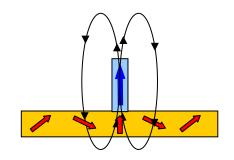


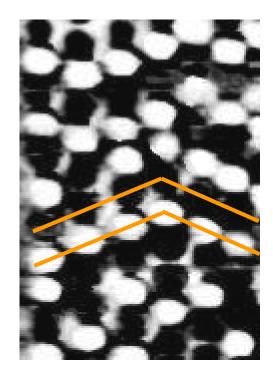
Interaction effects

Magnetic nanoparticles grown onto magnetic thin film:

- particle-particle interaction
- particle-thin film interaction
 - → magnetostatic, exchange

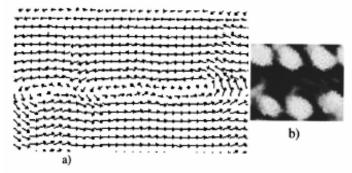






Enhanced interactions in particle array grown onto Permalloy

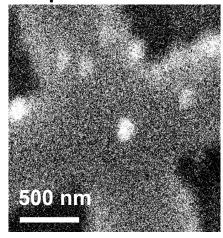
- → simultaneous switching events
- → metastable "stripe state"
- → magnetic domains in Permalloy



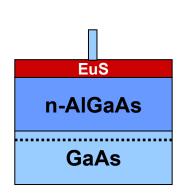
Wirth and von Molnár 2000, Christoph et al. 2001

"Simple" test system

sample 1



Single magnetic Fe particle grown onto EuS



concentrated magnetic semiconductor

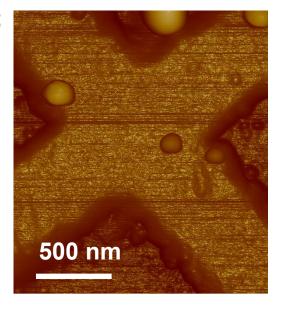
S = 7/2

EuS -

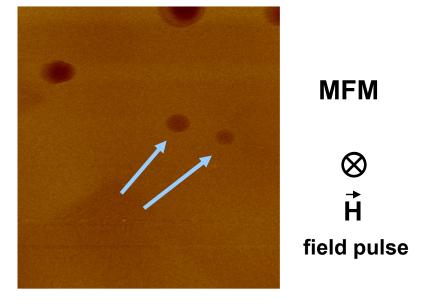
 $T_c \sim 17 \text{ K (insulating)}, \sim 25 \text{ K (conducting)}$

sample 2

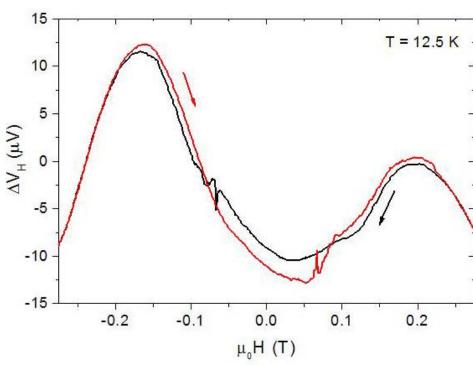
AFM



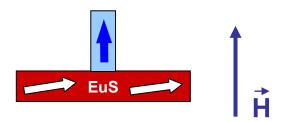
magnetization switching in MFM



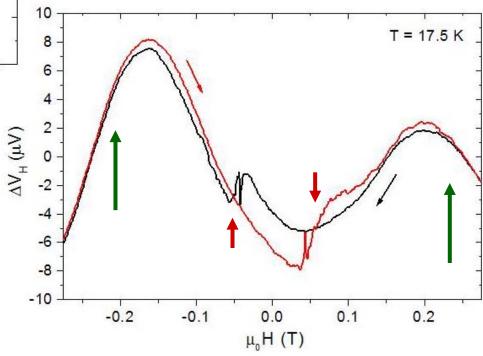
Single Fe particle on EuS

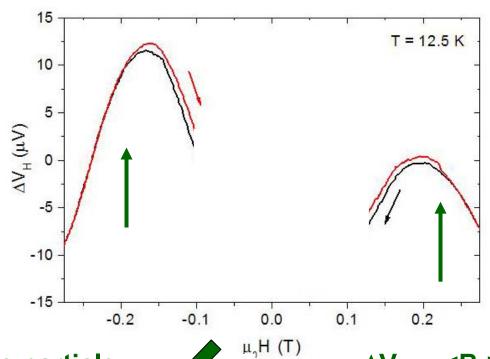


switching in EuS

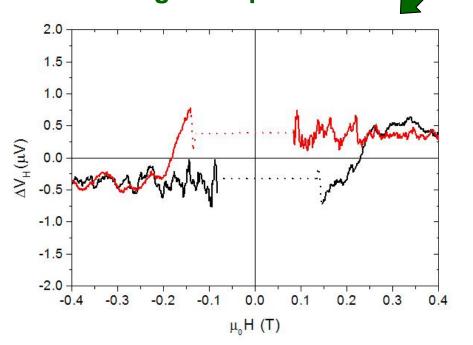


switching of Fe particle

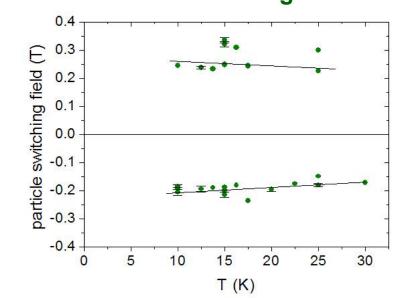


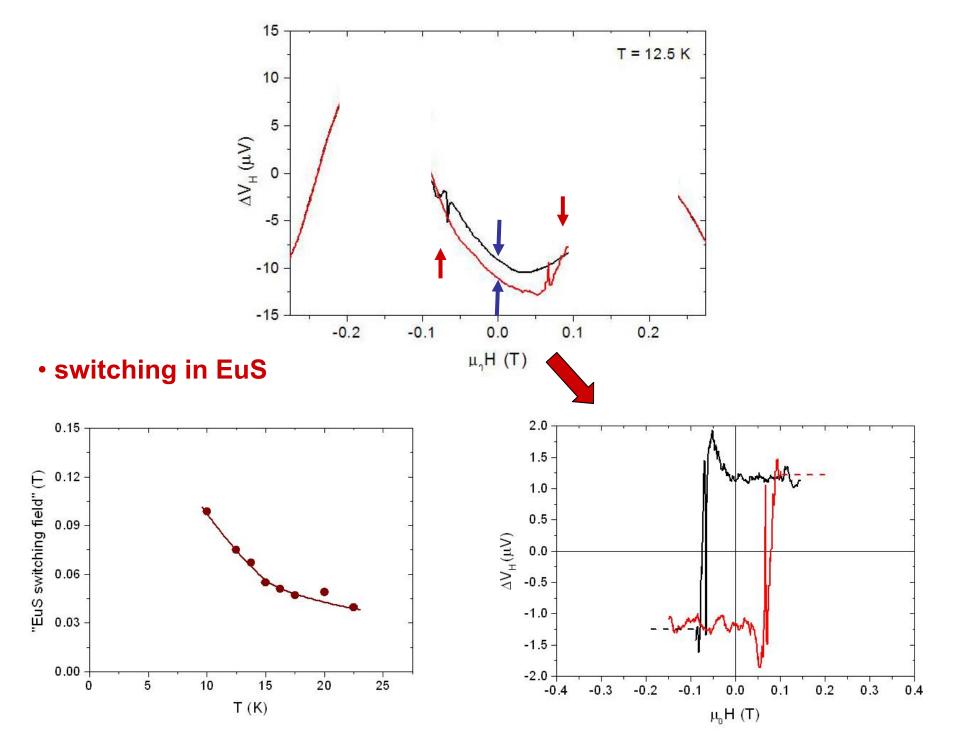


switching of Fe particle

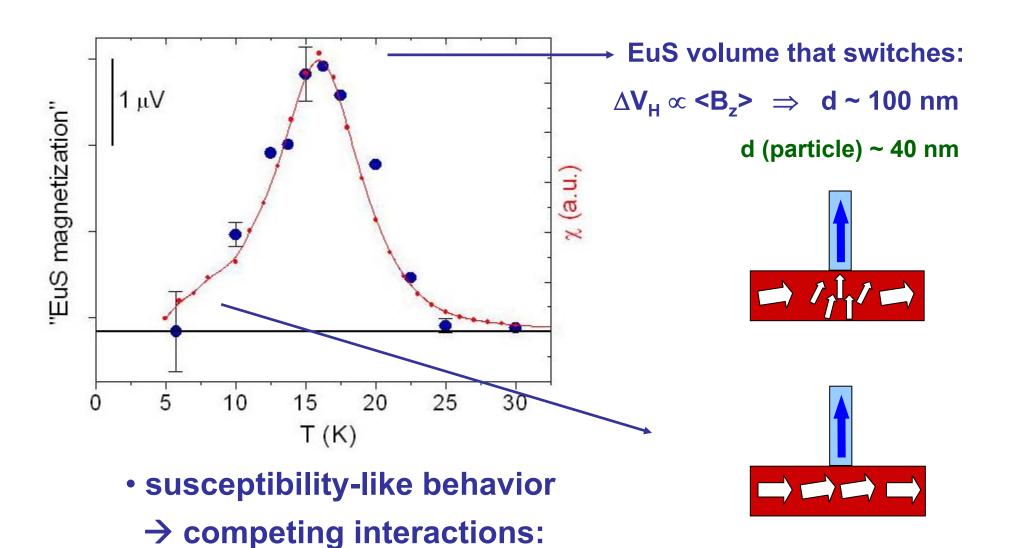


 $\Delta V_{H} \propto \langle B_{z} \rangle \implies d \sim 40 \text{ nm}$ \Rightarrow not single domain

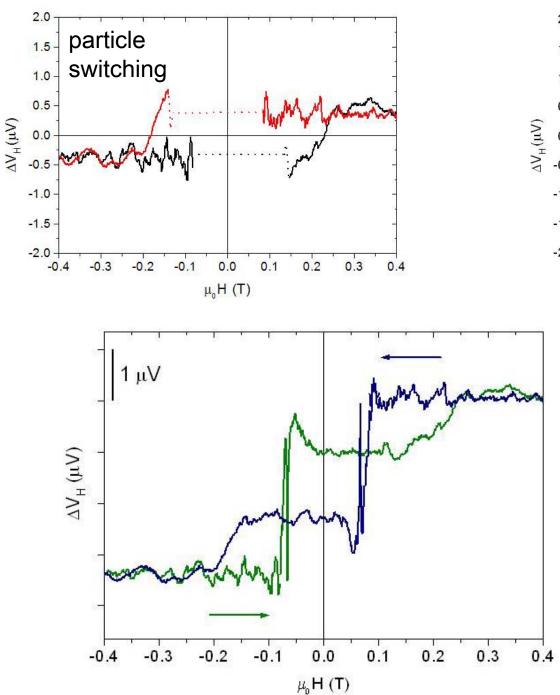


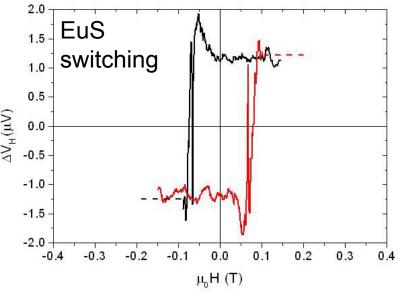


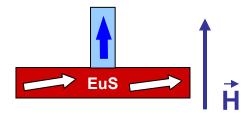
Single Fe particle on EuS



particle – EuS ←→ exchange in EuS



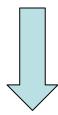




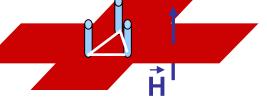
- switching contributions of nano-scale Fe particle and EuS thin film
 - + interaction effects
- complex magnetization behavior

Comments

- Single Fe particle on EuS study has shown that:
 - → Fe particle induces magnetization changes in EuS
 - → there exist complex competing magnetic interactions,
 - i.e. EuS-EuS vs. Fe-EuS, also Fe-EuS-Fe

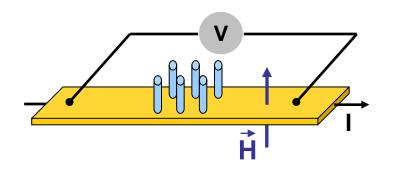




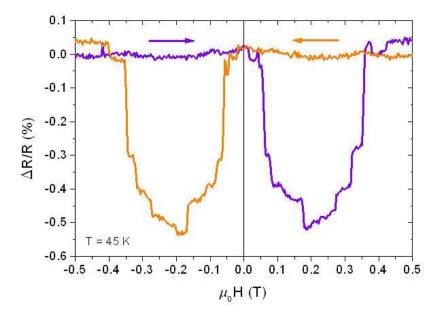


- → e.g. frustration on triangular lattic
- Transport: in substrate due to interactions

Transport

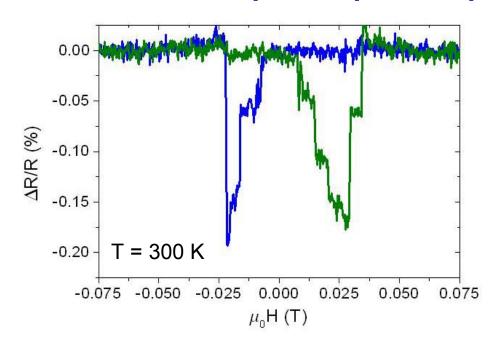


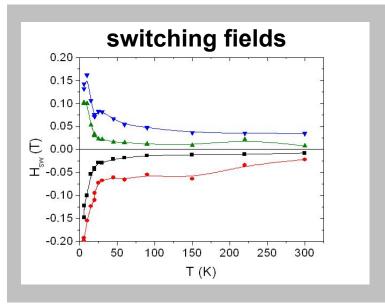
 modulation of transport in Py by particle's magnetization up to RT



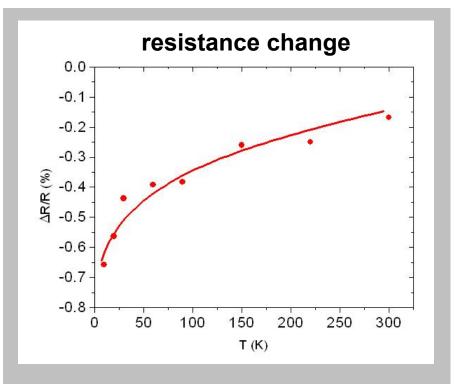
 engineering of transport properties of micro/nano-structured magnetic films using small and local magnetic flux sources

Transport of particle-permalloy heterostructure



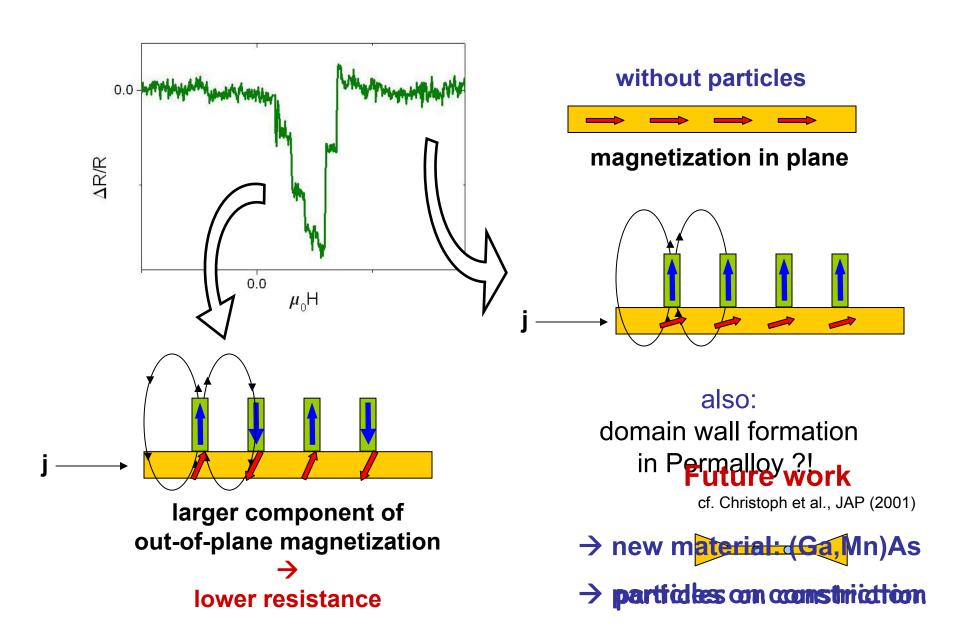


Temperature dependence



effect persists up to RT!

Explanation in terms of AMR?



Outline

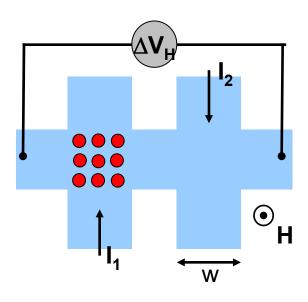
- I. Interaction effects at small scales
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Jens Müller

Materials by:

Hideo Ohno, Keita Ohtani (Tohoku University),

Improve moment sensitivity by miniaturization

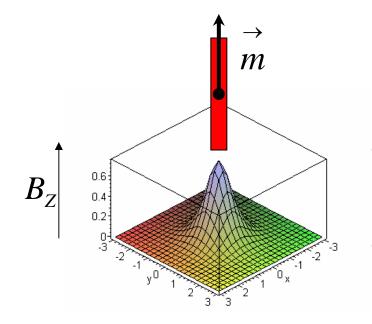


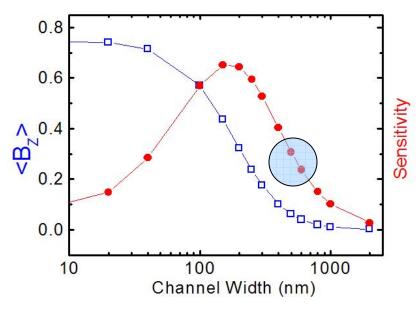
moment sensitivity: $m_{min} = C^{-1} \cdot B_{min}$

- coupling coefficient: C = <B_Z>/m
 - ⇒ miniaturization

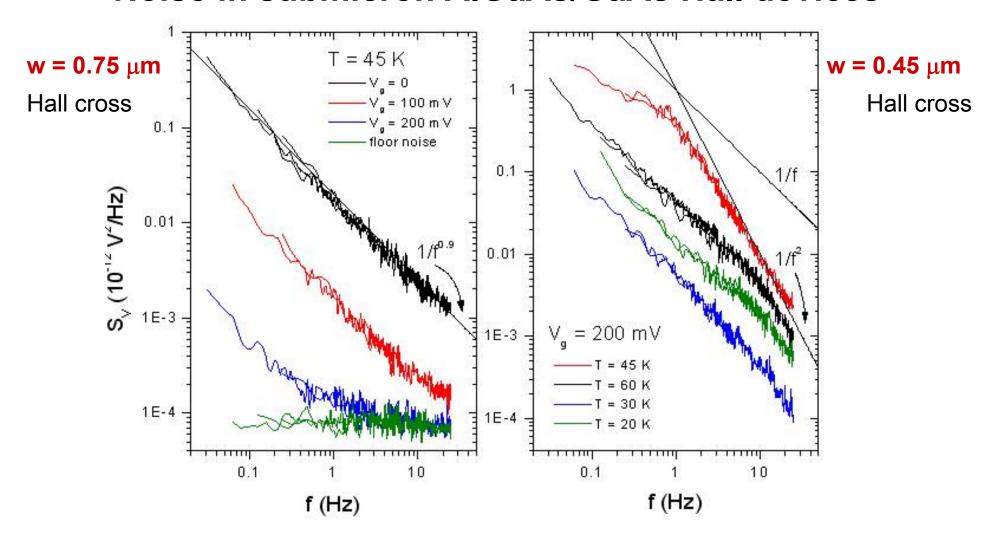
However:

- mesoscopic effects
- 1/f noise and telegraph noise
 - ⇒ *systematic* noise studies





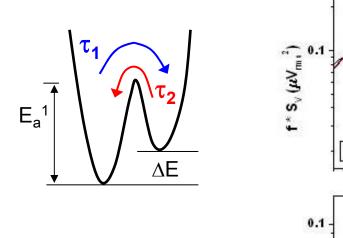
Noise in submicron AlGaAs/GaAs Hall devices



- large suppression of 1/f noise by gating
- moment sensitivity > $10^4 \mu_B/\sqrt{\text{Hz}}$ at 1 Hz and B = 0.25 T (10^{-16} emu)

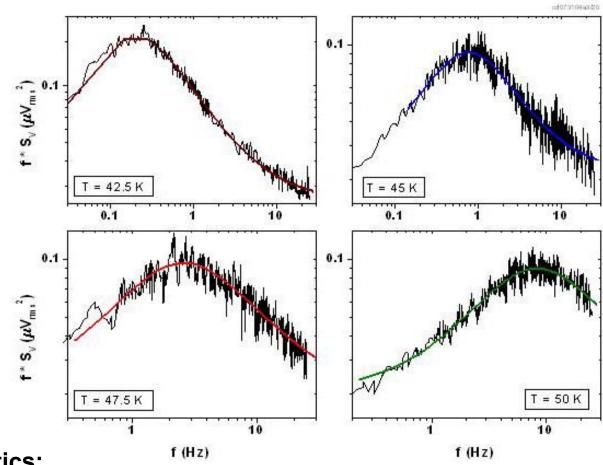
- non-monotonic T dependence
- deviations from 1/f
 - → Lorentzian-type spectra

Decomposition of 1/f noise



⇒ analyze $\mathbf{f} \times \mathbf{S}(\mathbf{f})$ ⇒ f_p , $f_p^2 \cdot \mathbf{S}(f_p)$

Kirtley et al., J. Appl. Phys. (1988)

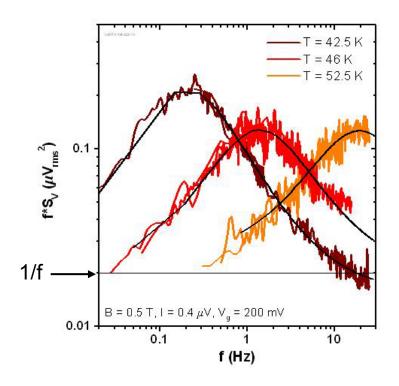


Two-rate fluctuator kinetics:

$$S(f) = \frac{4(\Delta V)^{2}}{\tau_{1} + \tau_{2}} \cdot \left(\frac{1}{(1/\tau_{p})^{2} + (2\pi f)^{2}}\right)$$

$$1/\tau_{p} = 2\pi f_{p} = 1/\tau_{1} + 1/\tau_{2}$$

Machlup, J. Appl. Phys. (1954)



- single fluctuator + (small) 1/f background
- thermally activated behavior

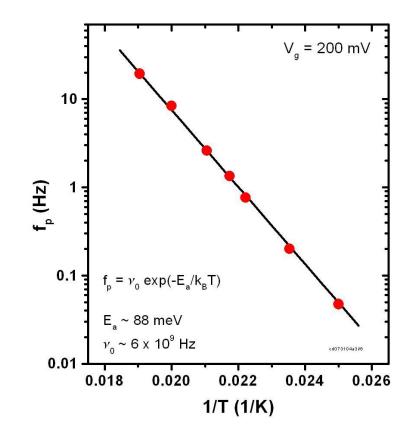
$$\tau_{i} = \nu_{0,i}^{-1} \cdot exp(E_{a,i} / k_{B}T)$$

electron trapping / emission:

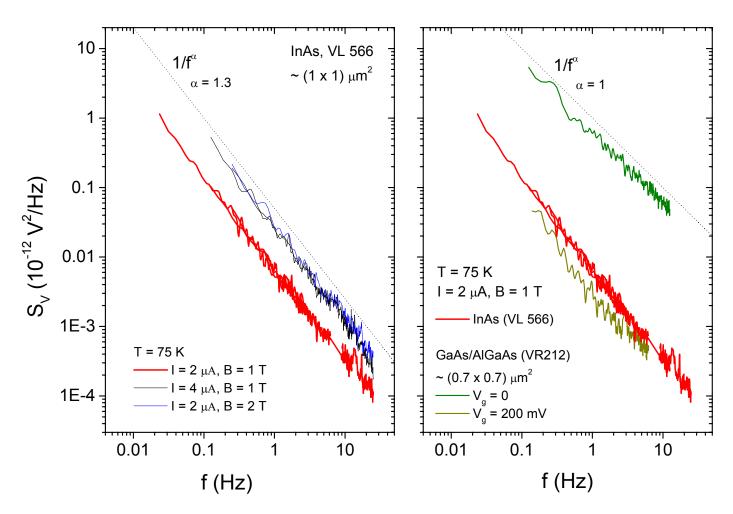
$$E_a \sim 88 \text{ meV}, \ v_0 \sim 6 \times 10^9 \text{ Hz}$$

Conclusions:

- gated submicron Hall devices excellent probes to study fluctuations in GaAs/Al_xGa_{1-x}As heterostructures
- random telegraph noise
 - → limits device miniaturization
- → restricts temperature range to below 100 K (trapping/detrapping of electrons from DX centers)



Hall devices from alternative semiconductors: InAs/AISb quantum well heterostructures



Noise level of *ungated* InAs device similarly low to that of Al_xGa_{1-x}As/GaAs devices where noise has been substantially suppressed by gating

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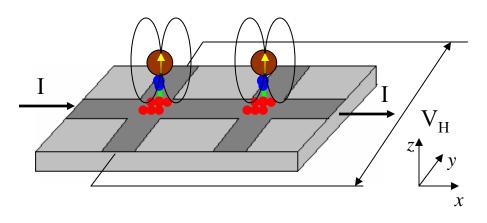
Goran Mihajlović, Pradeep Manandhar

Materials by:

Hideo Ohno & Keita Ohtani (Tohoku University),

Mark Field & Gerard J. Sullivan (Rockwell Scientific)

Hall sensor biological sensing scheme



- target molecule (analyte)
- complementary molecule
- magnetic particle (label) functionalized with complementary molecule

Magnetic labels should:

• be superparamagnetic to avoid aggregation in a sample solution

• have sizes comparable to the size of the target biomolecules

viruses: 20 - 450 nm

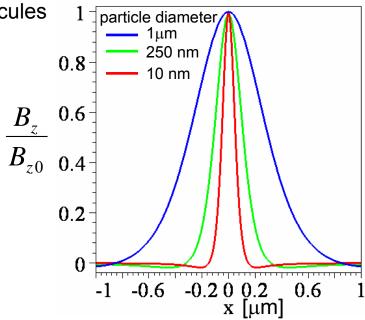
proteins: 5 - 50 nm

genes: $2nm \times 10 - 100 nm$

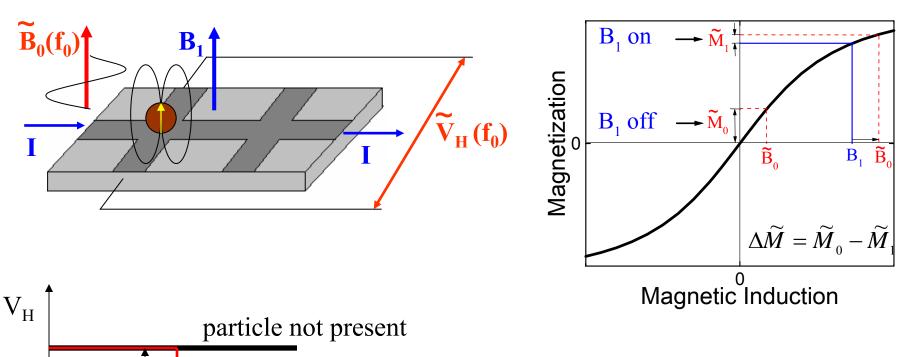
Q. A. Pankhurst et al., J. Phys. D 36, R167 (2003)

$$V_{
m H} \propto rac{1}{A} \int_A B_z dS$$

 \Rightarrow minimize A to maximize the signal!



Detection method for superparamagnetic particles



particle present

time

 $\Delta \widetilde{V}_{\!\scriptscriptstyle H}$

 B_1 on

- linear sensor output necessary to obtain definite information from one measurement
- $\Delta\widetilde{M}=f\left(\widetilde{B}_{0},B_{1}\right)$ \Rightarrow possibility for tuning the the signal to noise ratio by the applied fields

Micro-Hall sensors from InAs/AISb quantum well heterostructures

 $In_{0.5}Al_{0.5}As (5 nm)$

GaSb (0.6 nm)

A1Sb (13 nm)

InAs QW (12.5 nm)

AlSb (8 nm)

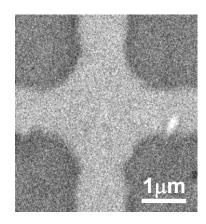
 $Al_{0.7}Ga_{0.3}Sb (1000 nm)$

AlSb (30 nm)

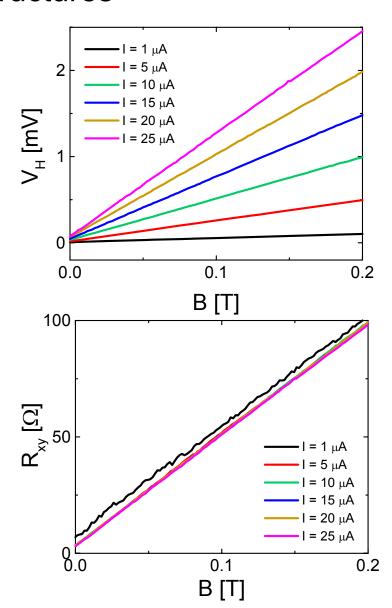
AlAs (30nm)

GaAs buffer (100 nm)

GaAs substrate



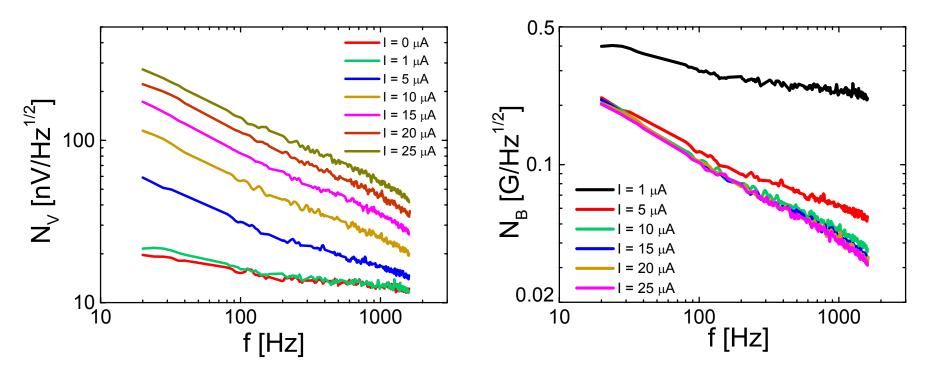
 $470 \Omega/T < R_H < 620 \Omega/T$



Magnetic field resolution of the micro-Hall sensors

- minimum uniform magnetic field that can be detected by the device
- ultimately limited by the device noise level at a maximum bias current $B_{\min} = \frac{r_{\text{HN}}}{R_{\text{H}}I_{\text{max}}}$

•
$$V_{\rm HN} = N_{\rm V} \sqrt{\Delta f}$$
 \Longrightarrow $B_{\rm min} = N_{\rm B} \sqrt{\Delta f}$



⇒ magnetic field resolution limited by 1/f noise!

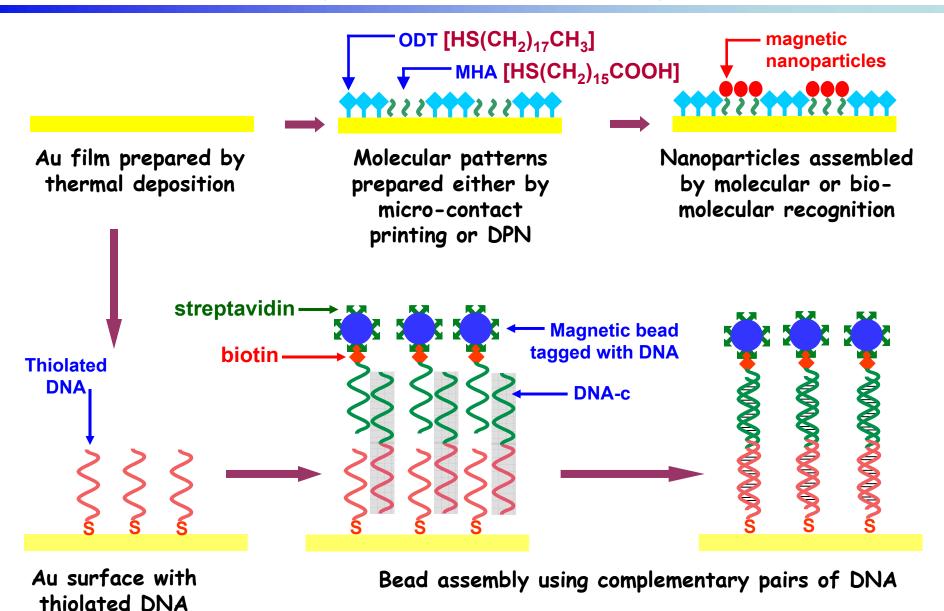
Detection of Single 1.2 µm Superparamagnetic Bead

G. Mihajlović et al., Appl. Phys. Lett. 87, 112502 (2005) V_{H1} V_{H2} V_{H2

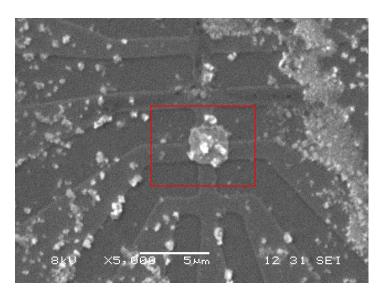
Detection parameters: $I = 10 \mu A$, $R_H = 616 \Omega/T$, $B_0 = 26.3 G$, $B_1 = 470 G$, $f_0 = 83.7 Hz$, $\tau = 1s$ Detected signal and noise level: $\Delta V_H = 1.35 \mu V$, $V_{HN} = 29 \text{ nV}$, S/N = 33.3 dB (46.5)Detected change in the stray magnetic field: $B_{det} = 2.2 G$

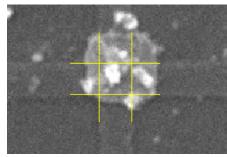
(Sigma Chemical CO)

Scheme for Assembly of Nanoparticles and Magnetic Beads



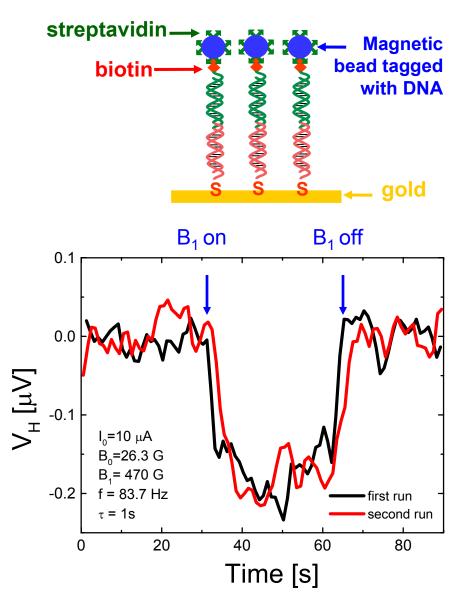
Detection of 250 nm Superparamagnetic Beads





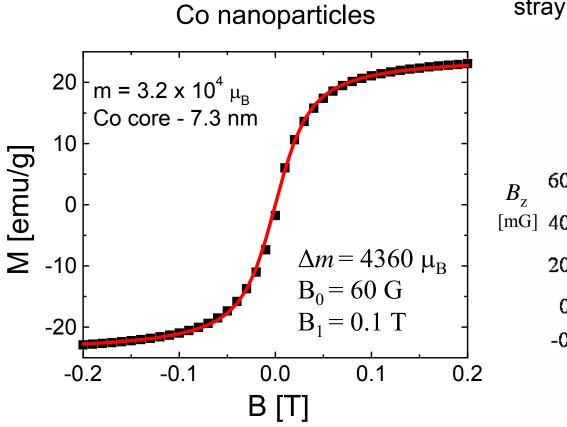
$$\Delta V_{\rm H} = 0.18 \; \mu \rm V$$

 $V_{\rm HN} = 23 \; \rm nV$
 $S/N = 17.9 \; \rm dB \; (7.8)$
 $B_{\rm det} = 0.30 \; \rm G$

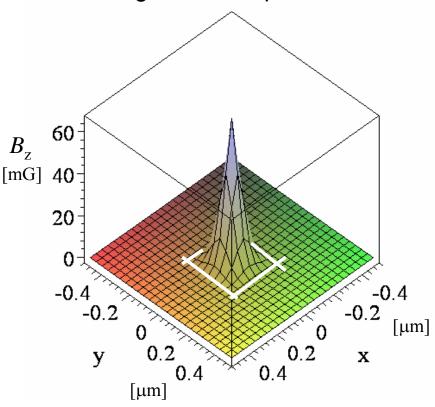


⇒ single nanobead sensitivity for 250 nm beads!

Are the smaller nanoparticles detectable?

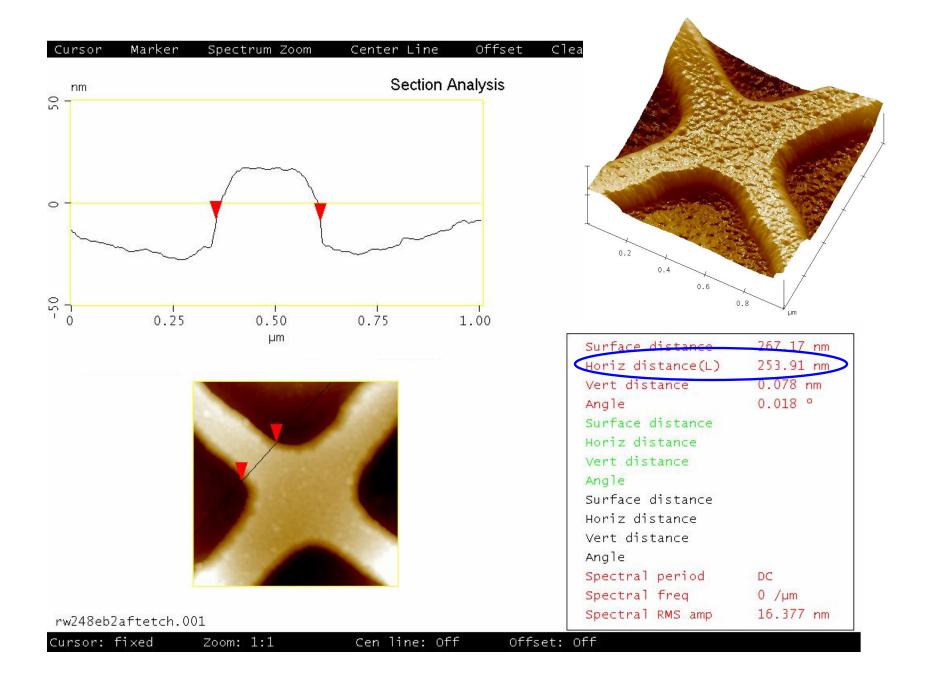


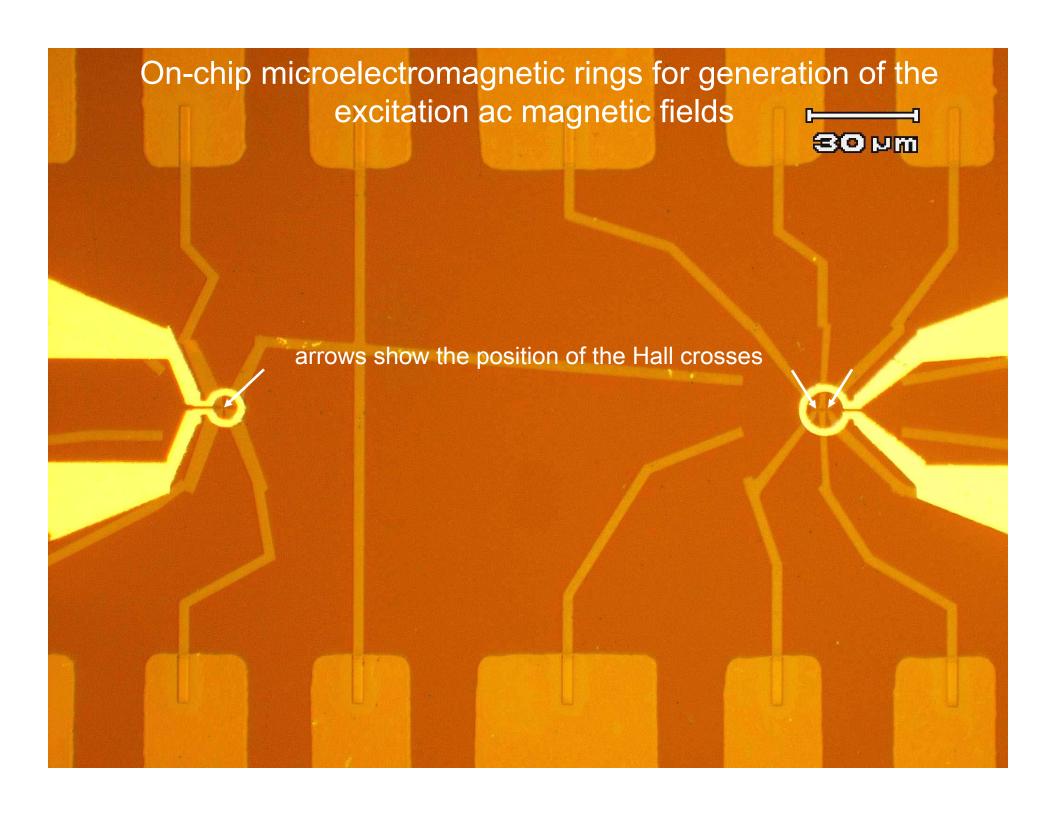
stray magnetic field distribution from a single Co nanoparticle



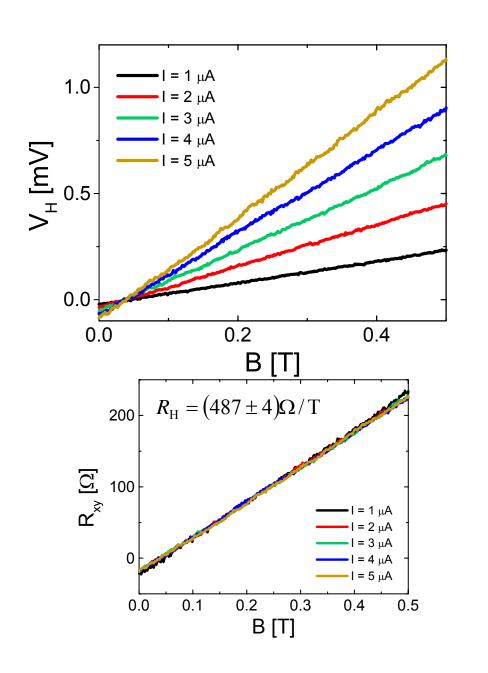
- average stray magnetic field flux from a single Co nanoparticle over the active area:
 - ~ 0.2 mG for 1 μ m \times 1 μ m Hall cross
 - ~ 10 mG for 300 nm × 300 nm Hall cross
 - ⇒ submicrometer Hall sensors!

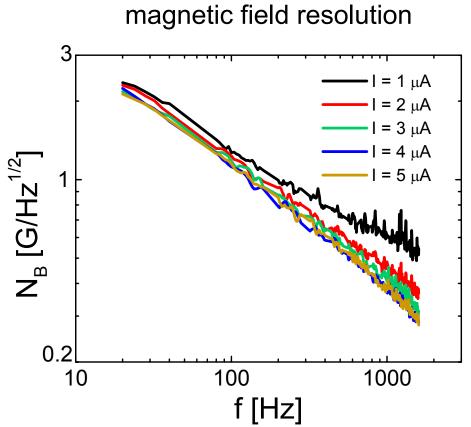
Fabrication of Submicrometer Hall sensors



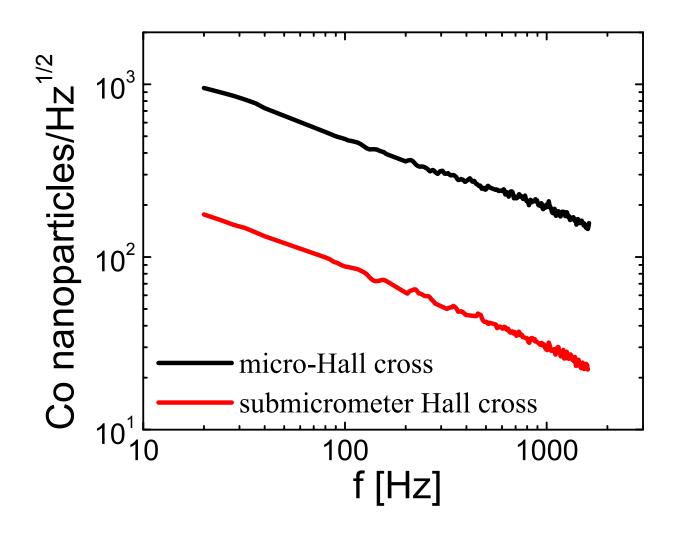


Functional submicrometer-Hall Sensors





Minimum detectable number of Co nanoparticles



100 Co nanoparticles = $4.36 \times 10^5 \mu_B$!

Conclusions

- micron and submicron Hall sensors from GaAs/AlGaAs heterostructures are excellent probes for the study nanomagnetism, including interaction effects.
- micron and submicron Hall sensors from InAs/AISb quantum well heterostructures are highly sensitive (moment sensitivities as much as ~10 5 μ_B at room temperature) detectors of micro- and nanobeads that can be utilized in biomolecular sensing.